Wuxi Unigroup Microelectronics Co.,Ltd

650V Super-junction Power MOSFET

Description

650V Super-junction Power MOSFET

Super-junction power MOSFET is a revolutionary technology for high voltage power MOSFETs，designed according to the SJ principle. The deep trench SJ MOSFET provide an extremely low switching, communication and conduction losses device with highest robustness make especially resonant switching applications more reliable, more efficient, lighter and cooler, designed by Wuxi Unigroup Microelectronics Company.

Features

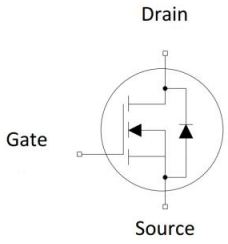
- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger

TO-220F

TO-252



RoHS

Device Marking and Package Information

Device	Package	Marking
TPA65R380D	TO-220F	65R380D
TPD65R380D	TO-252	65R380D

Key Performance Parameters

Parameter	Value	Unit
V_{DS} @ $T_{j,max}$	700	V
$R_{DS(on),max}$	0.38	Ω
$Q_{g,typ}$	17	nC
I_D	11	A
$I_{D,pulse}$	33	A
E_{OSS} @ 400V	2.14	μJ

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted				
Parameter		**Symbol**	**Values**	**Unit**
Continuous Drain Current	T_C = 25ºC	I_D	11	A
	T_C = 100ºC		6.6	
Pulsed Drain Current (note1)		$I_{D,pulse}$	33	A
Gate-Source Voltage		V_{GSS}	±30V	V
Single Pulse Avalanche Energy (note2)		E_{AS}	180	mJ
Repetitive Avalanche Energy (note2)		E_{AR}	0.5	mJ
Avalanche Current		I_{AR}	6	A
MOSFET dv/dt Ruggedness, V_{DS} = 0...480V		dv/dt	50	V/ns
Power Dissipation For TO-220F		P_D	24	W
Power Dissipation For TO-252			78	
Continuous Diode Forward Current		I_S	11	A
Diode Pulsed Current (note1)		$I_{S,pulse}$	33	
Reverse Diode dv/dt (note3)		dv/dt	5	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55~+150	ºC

Thermal Resistance For TO-220F			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	5.2	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Thermal Resistance For TO-252			
Parameter	**Symbol**	**Value**	**Unit**
Thermal Resistance, Junction-to-Case	R_{thJC}	1.6	ºC/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Electrical Characteristics T_J = 25ºC, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 650V, V_{GS} = 0V, T_J = 25ºC	--	--	1	μA
		V_{DS} = 650V, V_{GS} = 0V, T_J = 150ºC	--	--	100	
Gate-Source Leakage Current	I_{GSS}	V_{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.5	--	4.5	V
Drain-Source On-State-Resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 5.5A	--	0.33	0.38	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 50V, f = 1.0MHz	--	767	--	pF
Output Capacitance	C_{oss}		--	42	--	
Reverse Transfer Capacitance	C_{rss}		--	1.2	--	
Total Gate Charge	Q_g	V_{DD} = 520V, I_D = 20A, V_{GS} = 10V	--	17	--	nC
Gate-Source Charge	Q_{gs}		--	4.5	--	
Gate-Drain Charge	Q_{gd}		--	5.5	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 400V, I_D = 20A, R_G = 25Ω	--	49	--	ns
Turn-on Rise Time	t_r		--	21	--	
Turn-off Delay Time	$t_{d(off)}$		--	115	--	
Turn-off Fall Time	t_f		--	9	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	T_J = 25ºC, I_{SD} = 11A, V_{GS} = 0V	--	0.9	1.2	V
Reverse Recovery Time	t_{rr}	V_R = 400V, I_S=3A, di_F/dt = 100A/μs	--	260	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.7	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	16	--	A

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. I_D = 10A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. Identical low side and high side switch with identical R_G

Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 1. Output Characteristics

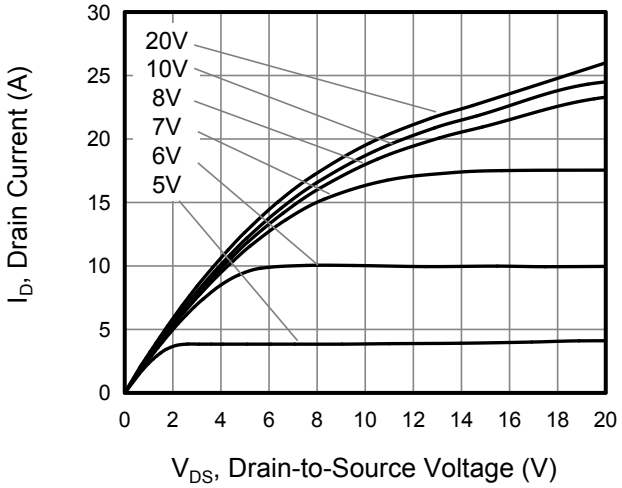


Figure 2. Transfer Characteristics

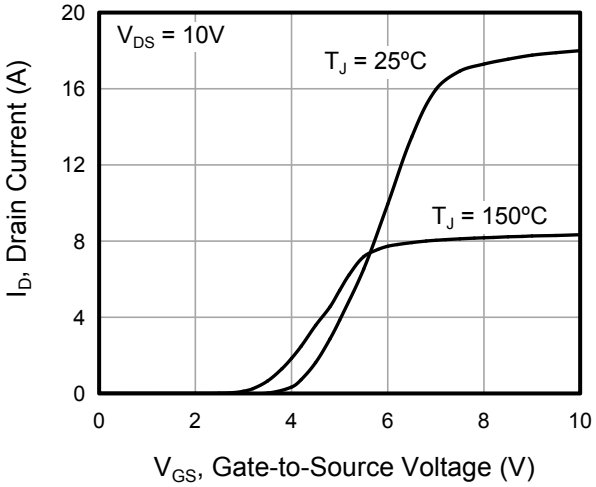


Figure 3. On-Resistance vs. Drain Current

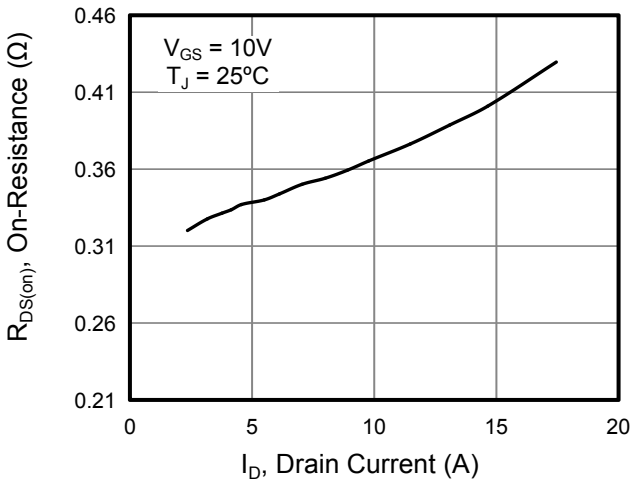


Figure 4. Capacitance

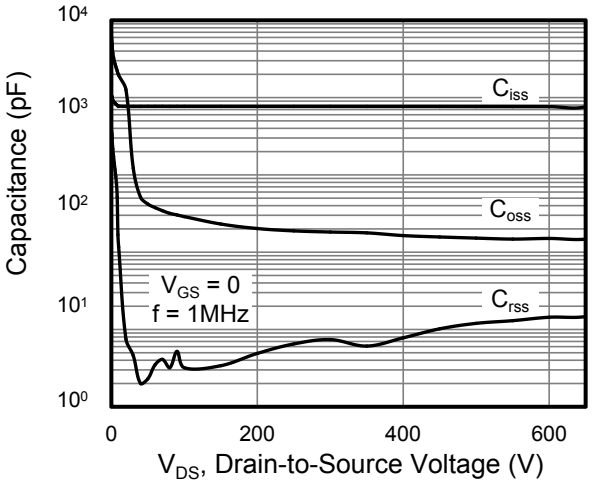


Figure 5. Gate Charge

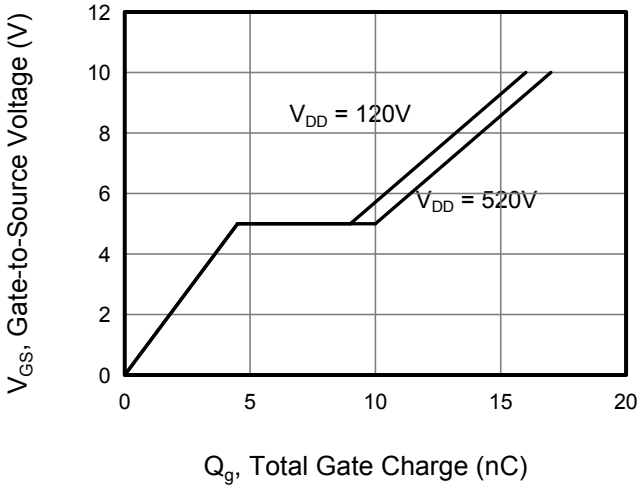


Figure 6. Body Diode Forward Voltage

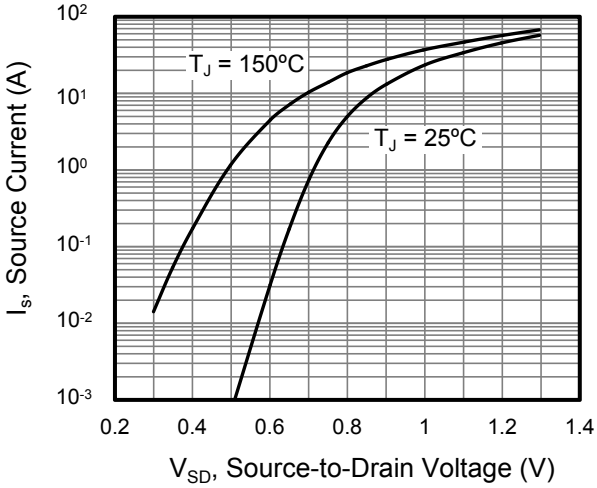


Figure 7. Breakdown voltage vs. Junction Temperature

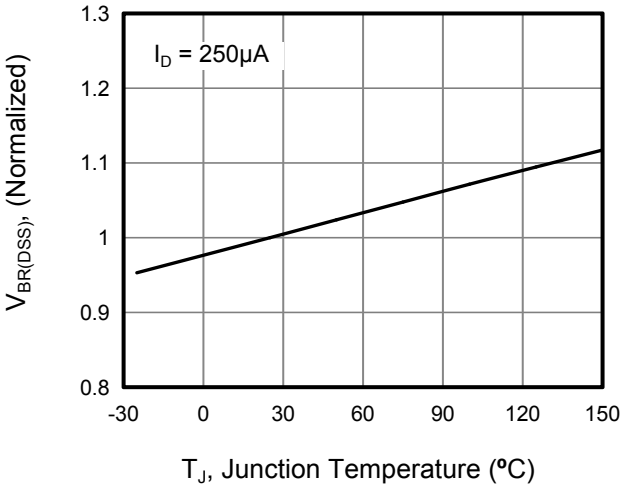


Figure 8. Threshold Voltage vs. Junction Temperature

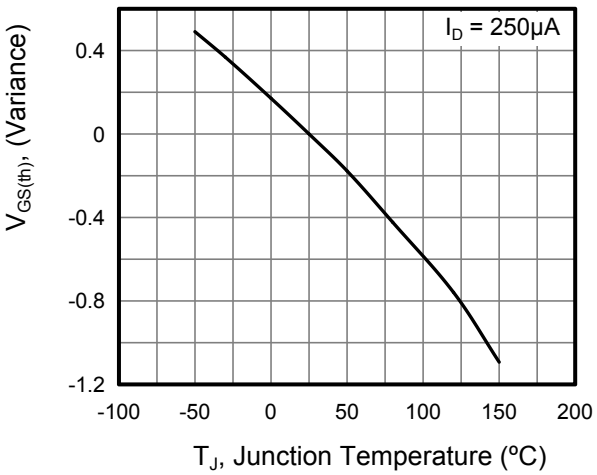


Figure 9. Transient Thermal Impedance For TO-252

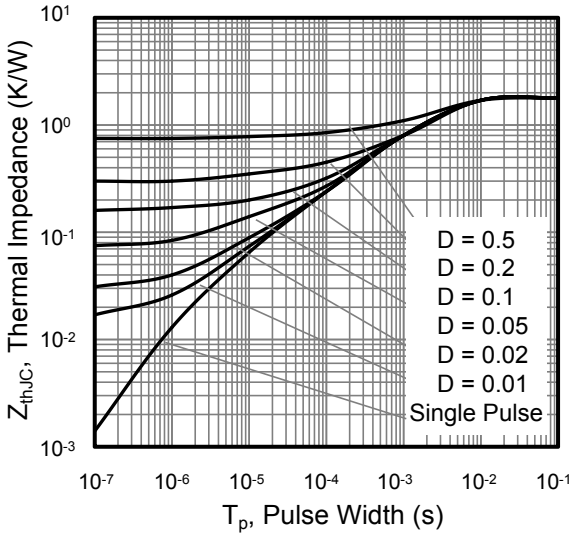


Figure 10. Transient Thermal Impedance For TO-220F

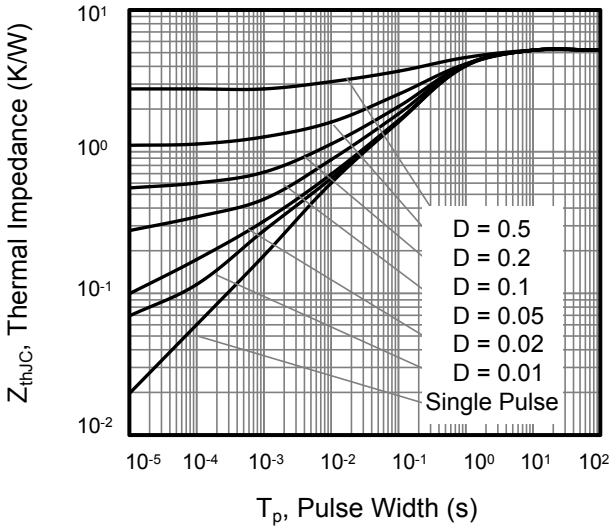


Figure 11. Safe Operation Area For TO-252

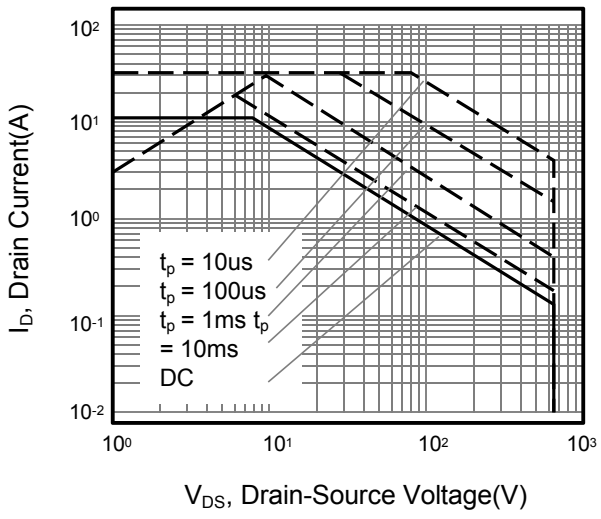
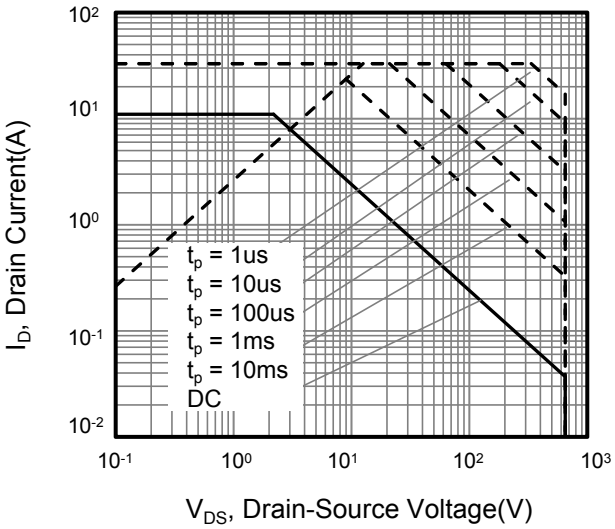


Figure 12. Safe Operation Area For TO-220F



Typical Characteristics T_J = 25ºC, unless otherwise noted

Figure 13. Typ. Coss Stored Energy

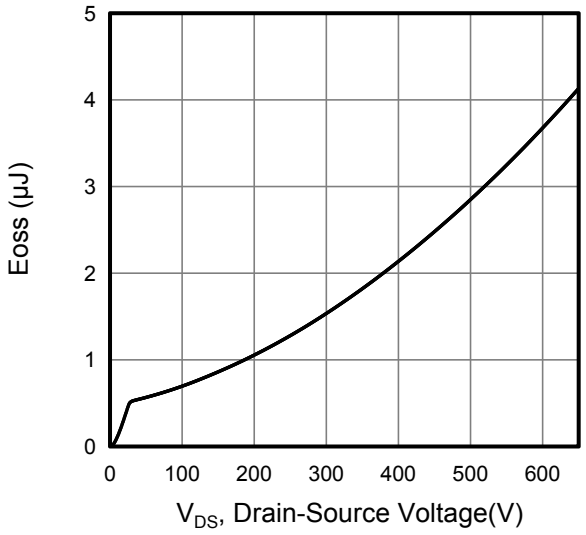


Figure A：Gate Charge Test Circuit and Waveform

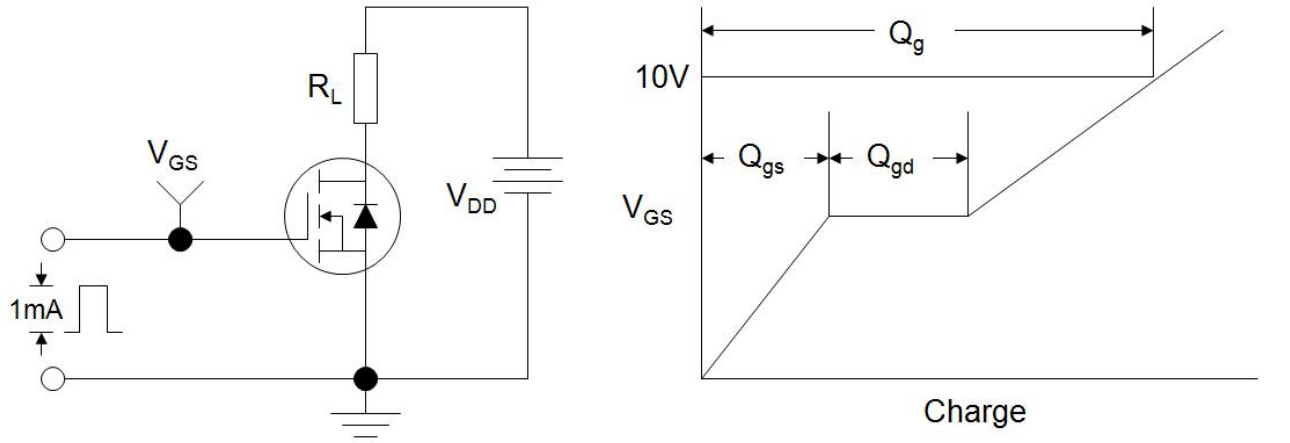


Figure B：Resistive Switching Test Circuit and Waveform

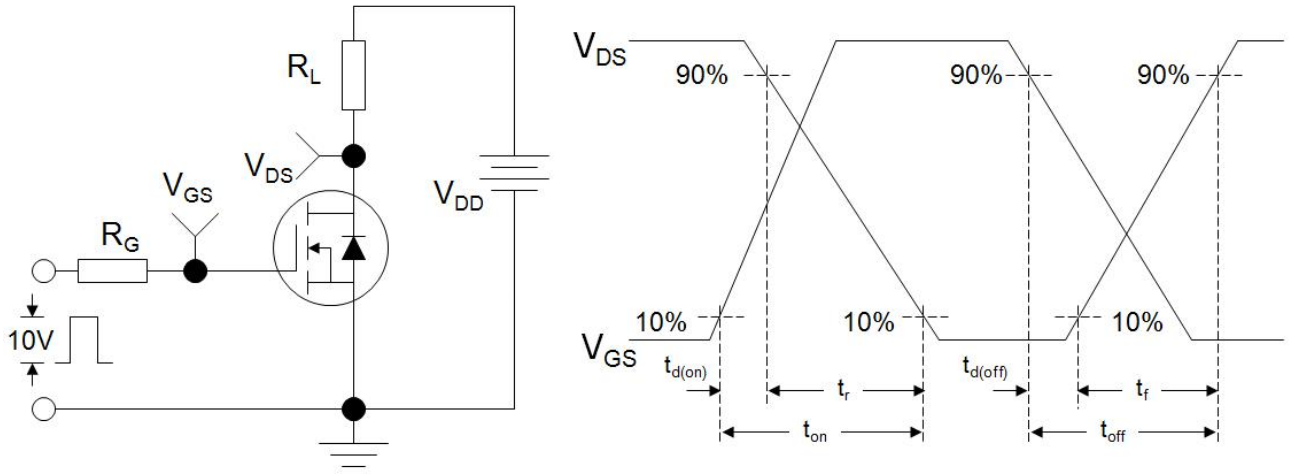
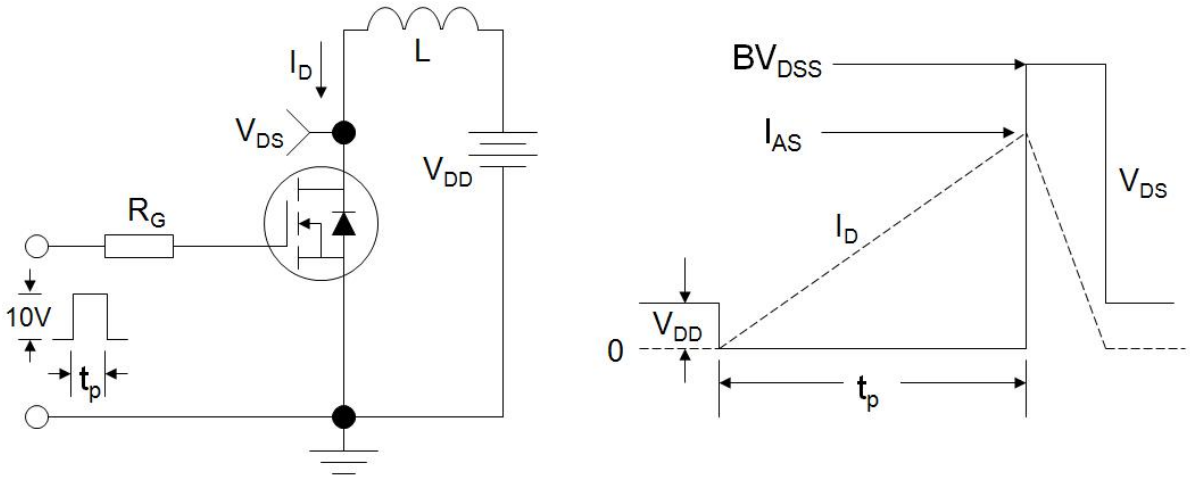
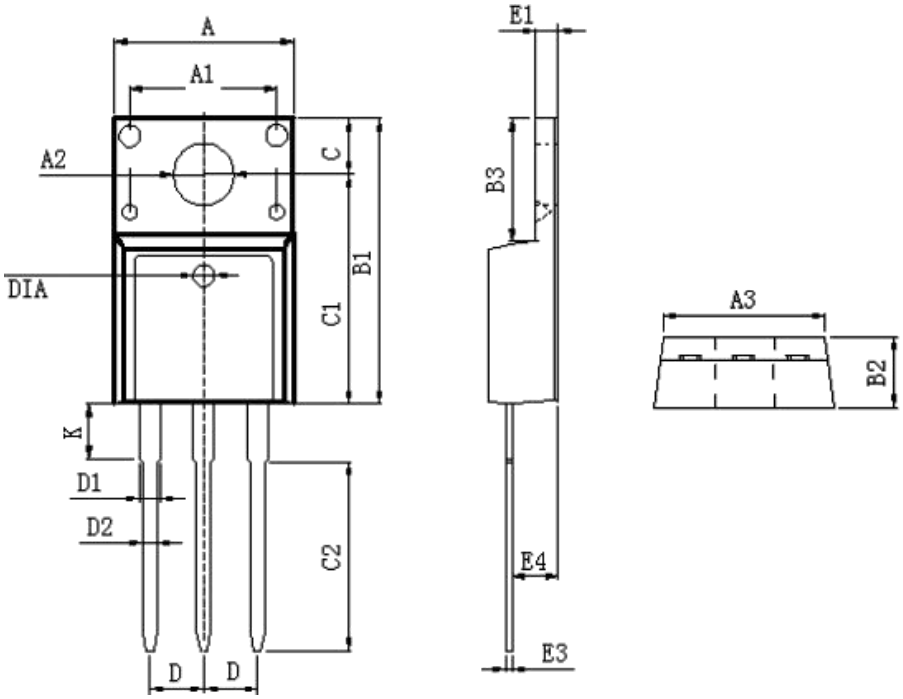


Figure C：Unclamped Inductive Switching Test Circuit and Waveform

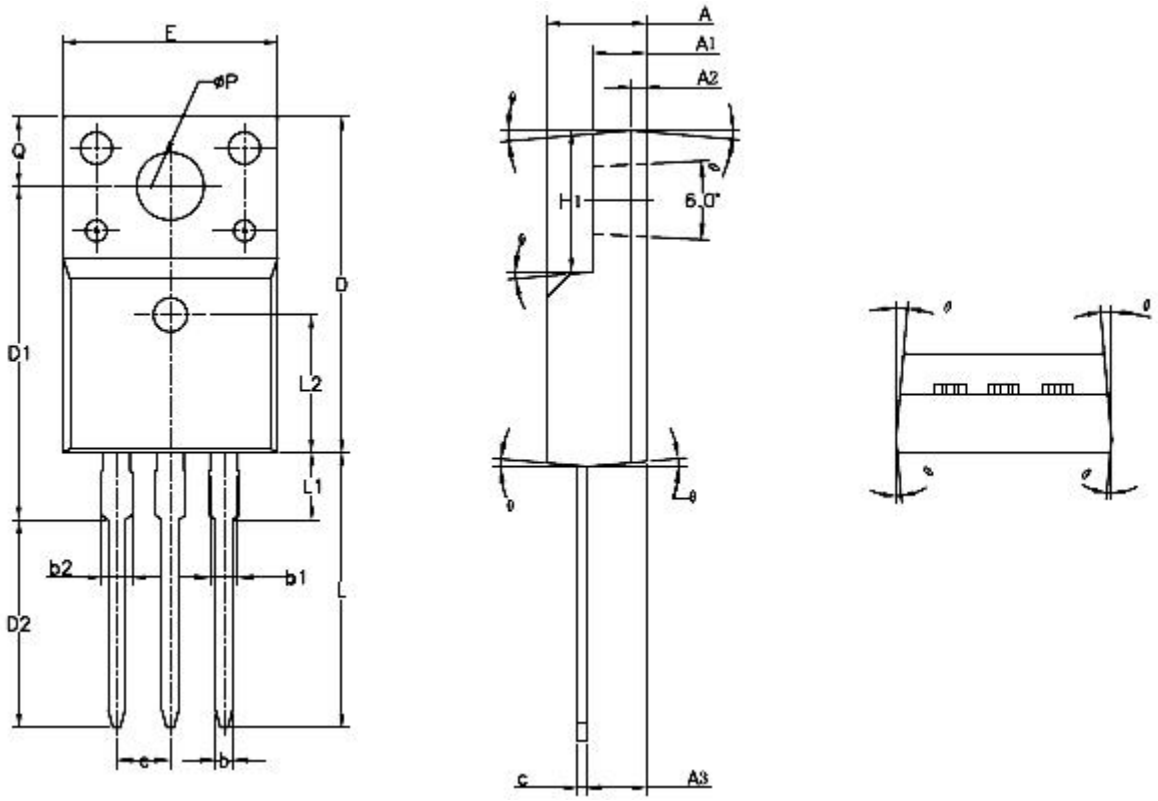


TO-220F（金田）



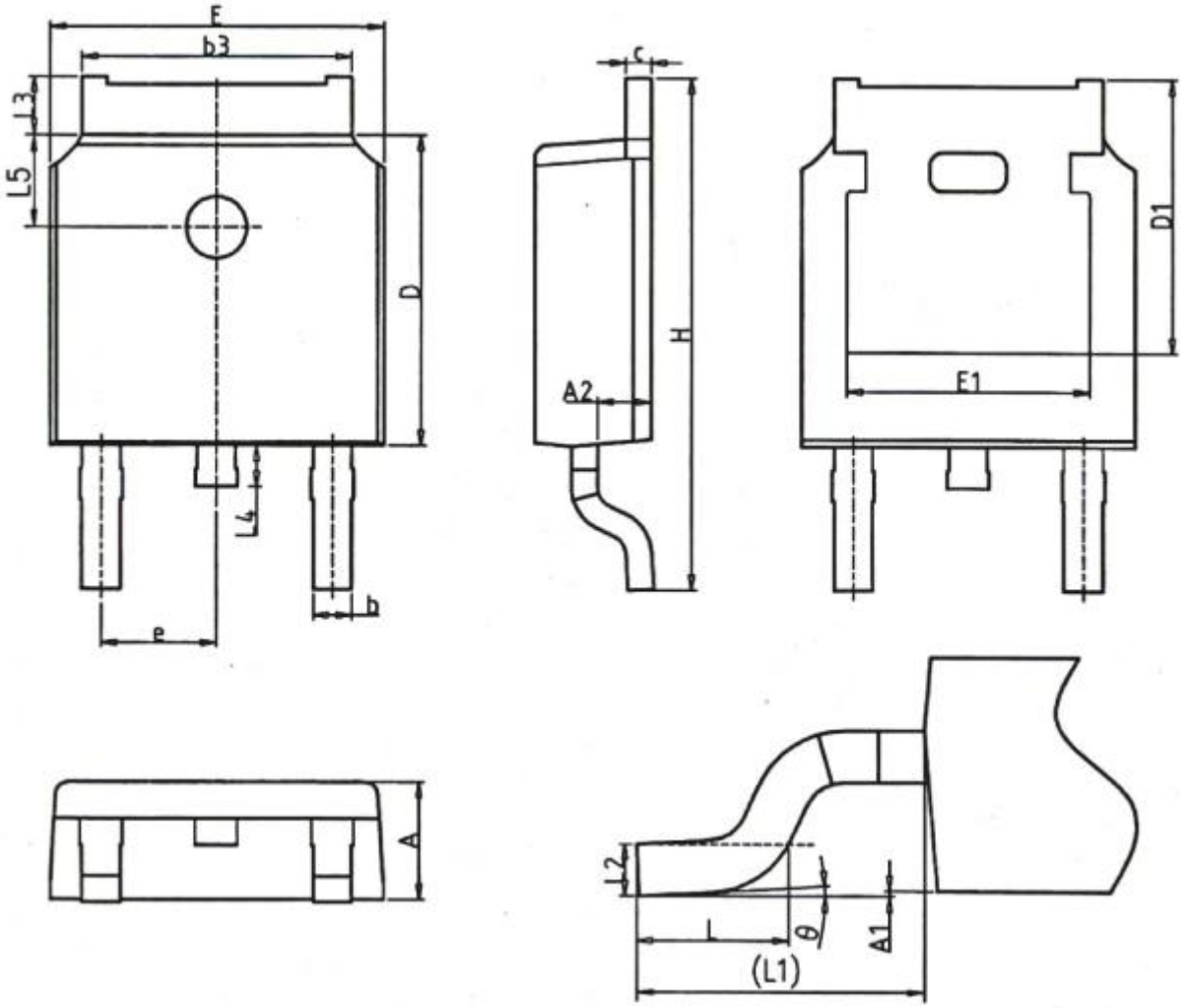
DIM	MILLIMETERS
A	10.16±0.3
A1	7.00±0.1
A2	3.3±0.2
A3	9.5±0.2
B1	15.87±0.3
B2	4.7±0.2
B3	6.68±0.4
C	3.3±0.2
C1	12.57±0.3
C2	10.02±0.5
D	2.54±0.05
D1	1.28±0.2
D2	0.8±0.1
K	3.1±0.3
E1	2.54±0.1
E3	0.5±0.1
E4	2.76±0.2
DIA	⊙1.5(deep 0.2)

TO-220F（集佳）



SYMBOL	MIN	NOM	MAX
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2		0.70 REF	
A3	2.56	2.76	2.93
b	0.70	–	0.90
b1	1.18	–	1.38
b2	–	–	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e		2.54BSC	
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	–	–	3.50
L2		6.50REF	
øP	3.08	3.18	3.28
Q	3.20	–	3.40
θ1	1°	3°	5°

TO-252（华羿）



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	546
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-

Unit:mm			
Symbol	Min.	Nom	Max.
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
θ	0°	-	8°

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